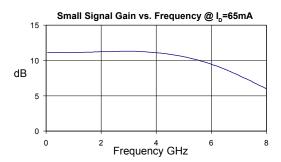


Product Description

Stanford Microdevices' SNA-686 is a high performance Gallium Arsenide Heterojunction Bipolar Transistor MMIC Amplifier. A Darlington configuration is utilized for broadband performance up to 6 GHz. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Typical IP3 at 850 MHz with 65mA is 34 dBm.

These unconditionally stable amplifiers provide 11 dB of gain and 17.7 dBm of 1dB compressed power and require only a single positive voltage supply. Only 2 DC-blocking capacitors, a bias resistor and an optional inductor are needed for operation. This MMIC is an ideal choice for wireless applications such as cellular, PCS, CDPD, wireless data and SONET.



SNA-686 DC-6 GHz, Cascadable **GaAs HBT MMIC Amplifier**

NGA-686 Recommended for New Designs



Product Features

- High Output IP3: 34 dBm @ 850 MHz
- Cascadable 50 Ohm Gain Block
- Patented GaAs HBT Technology
- Operates From Single Supply

Applications

• Cellular, PCS, CDPD, Wireless Data, SONET

Flactrical Specifications

| Electrical S | pecifications | | | | | |
|------------------|---|---|-------------------|------|----------------------|------|
| Symbol | Parameters: Test Conditions: $Z_0 = 50$ Ohms, $I_D = 65$ mA, $T = 25$ °C | | Units | Min. | Тур. | Max. |
| P _{1dB} | Output Power at 1dB Compression | f = 850 MHz f = 1950 MHz f = 2400 MHz | dBm dBm dBm | | 17.6 17.7 17.4 | |
| IP ₃ | Third Order Intercept Point Power out per tone = 0 dBm | f = 850 MHz f = 1950 MHz f = 2400 MHz | dBm dBm dBm | | 34.0 32.1 30.0 | |
| S ₂₁ | Small Signal Gain | f = 850 MHz f = 1950 MHz f = 2400 MHz | dB dB dB | 10 | 11.1 11.2 11.3 | |
| Bandwidth | (Determined by S ₁₁ , S ₂₂ Values) | | MHz | | 6000 | |
| S ₁₁ | Input VSWR | f = DC-6000 MHz | - | | 1.3:1 | |
| S ₂₂ | Output VSWR | f = DC-6000 MHz | - | | 1.4:1 | |
| S ₁₂ | Reverse Isolation | f = 850 MHz f = 1950 MHz f = 2400 MHz | dB dB dB | | 16.3 16.5 16.6 | |
| NF | Noise Figure, Z _s = 50 Ohms | f = 1950 MHz | dB | | 7.3 | |
| V _D | Device Voltage | | V | 4.8 | 5.3 | 5.8 |
| Rth,j-I | Thermal Resistance (junction - lead) | | ° C/W | | 261 | |

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Absolute Maximum Ratings

Operation of this device above any one of these parameters may cause permanent damage.

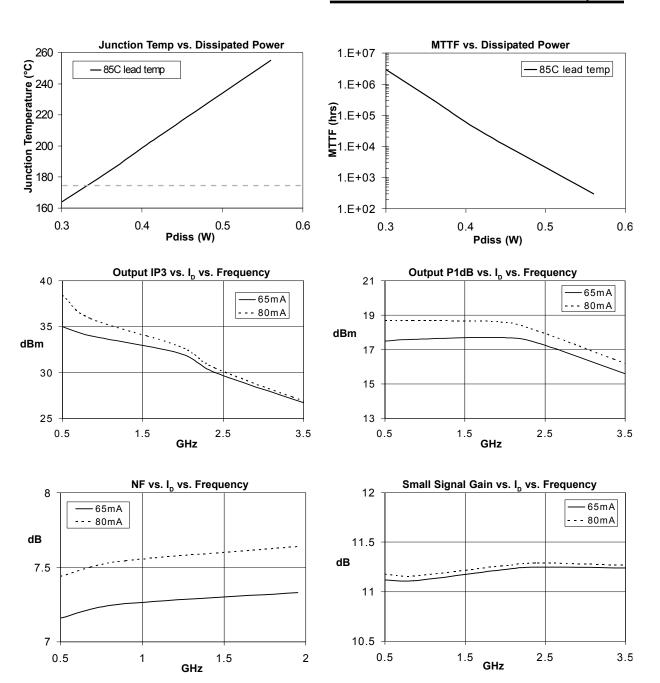
Bias Conditions should also satisfy the following expression: I_pV_p (max) < $(T_1 - T_{OP})/Rth$, j-I

| Parameter | Value | Unit |
|--------------------------------|-------------|------|
| Supply Current | 120 | mA |
| Operating Temperature | -40 to +85 | С |
| Maximum Input Power | 16 | dBm |
| Storage Temperature Range | -40 to +150 | С |
| Operating Junction Temperature | +175 | С |

| Parameter | Typical 25°C | Unit | Test Condition |
|-------------------|-----------------|-------|--|
| | 25 0 | Offic | (I _D = 65 mA, unless otherwise noted) |
| 500 MHz | 44.4 | -10 | |
| Gain | 11.1 | dB | 7 50 Okaza |
| Noise Figure | 7.2 | dB | $Z_s = 50 \text{ Ohms}$ |
| Output IP3 | 35.0 | dBm | Tone spacing = 1 MHz, Pout per tone = 0 dBm |
| Output P1dB | 17.5 | dBm | |
| Input Return Loss | 25.2 | dB | |
| Isolation | 16.2 | dB | |
| 850 MHz | | | |
| Gain | 11.1 | dB | |
| Noise Figure | 7.3 | dB | $Z_s = 50 \text{ Ohms}$ |
| Output IP3 | 34.0 | dBm | Tone spacing = 1 MHz, Pout per tone = 0 dBm |
| Output P1dB | 17.6 | dBm | |
| Input Return Loss | 22.3 | dB | |
| Isolation | 16.3 | dB | |
| 1950 MHz | | | |
| Gain | 11.2 | dB | |
| Noise Figure | 7.3 | dB | $Z_s = 50 \text{ Ohms}$ |
| Output IP3 | 32.1 | dBm | Tone spacing = 1 MHz, Pout per tone = 0 dBm |
| Output P1dB | 17.7 | dBm | , , , |
| Input Return Loss | 19.6 | dB | |
| Isolation | 16.5 | dB | |
| 2400 MHz | | | |
| Gain | 11.3 | dB | |
| Output IP3 | 30.0 | dBm | Tone spacing = 1 MHz, Pout per tone = 0 dBm |
| Output P1dB | 17.4 | dBm | |
| Input Return Loss | 18.4 | dB | |
| Isolation | 16.6 | dB | |

***NOTE:** While the SNA-686 can be operated at different bias currents, 65 mA is the recommended bias for lower junction temperature and longer life. This reflects typical operating conditions which we have found to be an optimal balance between high IP3 and MTTF. In general, MTTF is improved to more than 100,000 hours when biasing at 65 mA and operating up to 85°C ambient temperature.

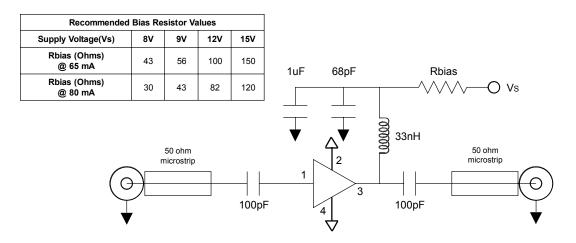




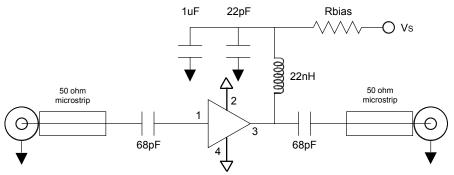


| Pin # | Function | Description |
|-------|------------|---|
| 1 | RF IN | RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation. |
| 2 | GND | Connection to ground. Use via holes for best performance to reduce lead inductance. Place vias as close to ground leads as possible. |
| 3 | RF OUT/Vcc | RF output and bias pin. Bias should be supplied to this pin through an external series resistor and RF choke inductor. Because DC biasing is present on this pin, a DC blocking capacitor should be used in most applications (see application schematic). The supply side of the bias network should be well bypassed. |
| 4 | GND | Same as Pin 2. |

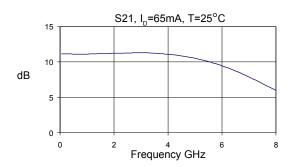
Application Schematic for Operation at 850 MHz

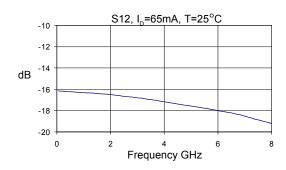


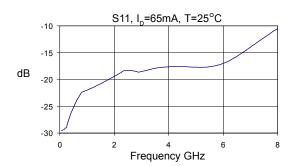
Application Schematic for Operation at 1950 MHz

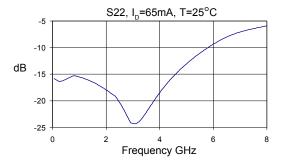


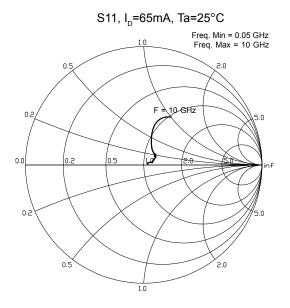


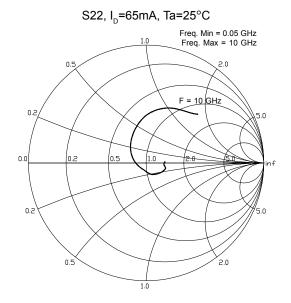




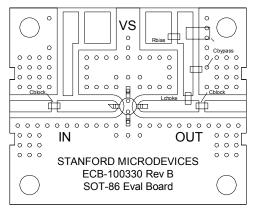












Part Number Ordering Information

| Part Number | Reel Size | Devices/Reel | |
|-------------|-----------|--------------|--|
| SNA-686 | 7" | 1000 | |



Caution ESD Sensitive:

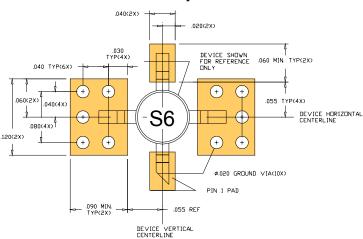
Appropriate precautions in handling, packaging and testing devices must be observed.

Part Symbolization

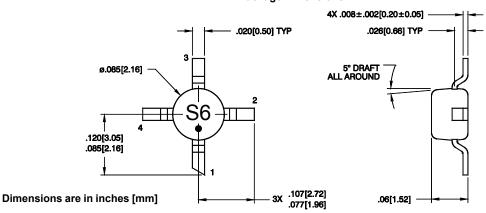
The part will be symbolized with an "S6" designator on the top surface of the package.

Evaluation Board Layout

PCB Pad Layout



Package Dimensions



EDS-101398 Rev A